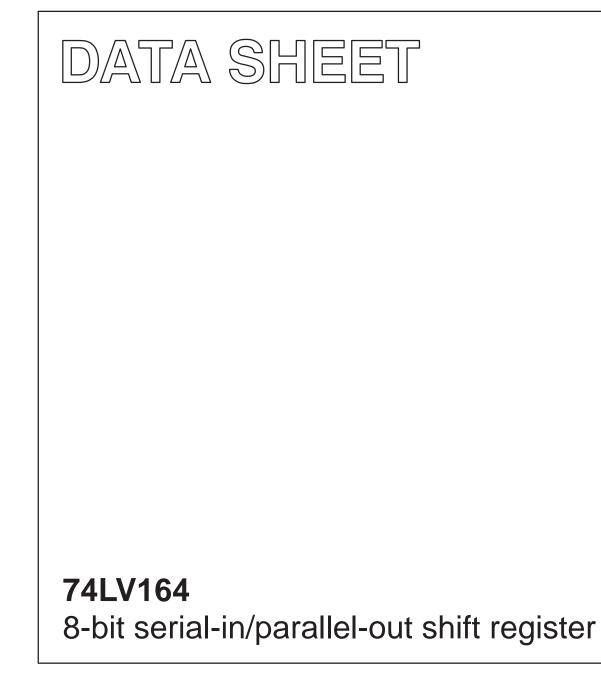
INTEGRATED CIRCUITS



Product specification Supersedes data of 1996 Feb IC24 Data Handbook 1997 Mar 28





74LV164

FEATURES

- Wide operating voltage: 1.0 to 5.5V
- Optimized for Low Voltage applications: 1.0 to 3.6V
- Accepts TTL input levels between V_{CC} = 2.7V and V_{CC} = 3.6V
- Typical V_{OLP} (output ground bounce) < 0.8V @ V_{CC} = 3.3V, $T_{amb} = 25^{\circ}C$
- Typical V_{OHV} (output V_{OH} undershoot) > 2V @ V_{CC} = 3.3V, T_{amb} = 25°C
- DC triggered from active HIGH or active LOW inputs
- Gated serial data inputs
- Asynchronous master reset
- Output capability: standard
- I_{CC} category: MSI

QUICK REFERENCE DATA

GND = 0V; $T_{amb} = 25^{\circ}C$; $t_r = t_f \le 2.5$ ns

DESCRIPTION

The 74LV164 is a low-voltage Si-gate CMOS device and is pin and function compatible with the 74HC/HCT164.

The 74LV164 is an 8-bit edge-triggered shift register with serial data entry and an output from each of the eight stages.Data is entered serially through one of two inputs (D_{sa} or D_{sb}); either input can be used as an active HIGH enable for data entry through the other input. Both inputs must be connected together or an unused input must be tied HIGH.

Data shifts one place to the right on each LOW-to-HIGH transition of the clock (CP) input and enters into Q0, which is the logical AND of the two data inputs (D_{sa} , D_{sb}) that existed one set–up time prior to the rising clock edge.

A LOW on the master reset (MR) input overrides all other inputs and clears the register asynchronously, forcing all outputs LOW.

SYMBOL	PARAMETER	CONDITIONS	TYPICAL	UNIT
t _{PHL} /t _{PLH}	Propagation delay CP to Q _n MR to Q _n	C _L = 15pF V _{CC} = 3.3V	12 12	ns
f _{max}	Maximum clock frequency		78	MHz
Cl	Input capacitance		3.5	pF
C _{PD}	Power dissipation capacitance per gate	V _{CC} = 3.3V Notes 1 and 2	40	pF

NOTES:

1. C_{PD} is used to determine the dynamic power dissipation (P_D in μ W) P_D = C_{PD} × V_{CC}² x f_i + Σ (C_L × V_{CC}² × f_o) where: f_i = input frequency in MHz; C_L = output load capacity in pF; f_o = output frequency in MHz; V_{CC} = supply voltage in V;

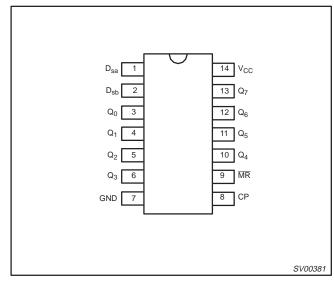
- Σ (C_L × V_{CC}² × f₀) = sum of the outputs.
- 2. The condition is $V_I = GND$ to V_{CC}

ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	PKG. DWG. #
14-Pin Plastic DIL	–40°C to +125°C	74LV164 N	74LV164 N	SOT27-1
14-Pin Plastic SO	–40°C to +125°C	74LV164 D	74LV164 D	SOT108-1
14-Pin Plastic SSOP Type II	–40°C to +125°C	74LV164 DB	74LV164 DB	SOT337-1
14-Pin Plastic TSSOP Type I	–40°C to +125°C	74LV164 PW	74LV164PW DH	SOT402-1

74LV164

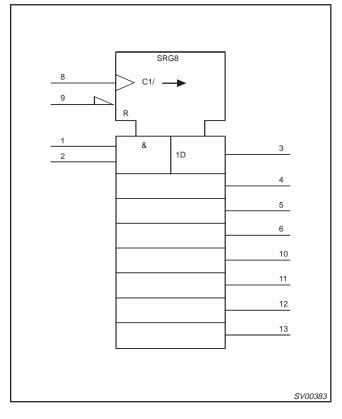
PIN CONFIGURATION



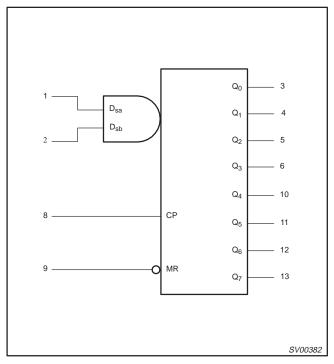
PIN DESCRIPTION

PIN NUMBER	SYMBOL	FUNCTION
1,2	D _{sa} , D _{sb}	Data inputs
3, 4, 5, 6, 10, 11, 12, 13	Q_0 to Q_7	Outputs
7	GND	Ground (0V)
8	CP	Clock input (LOW-to-HIGH, edge-trig- gered)
9	MR	Master reset input (active LOW)
14	V _{CC}	Positive supply voltage

LOGIC SYMBOL (IEEE/IEC)

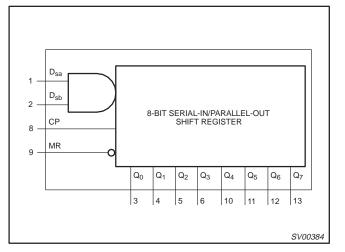


LOGIC SYMBOL



74LV164

FUNCTIONAL DIAGRAM



ABSOLUTE MAXIMUM RATINGS^{1, 2}

In accordance with the Absolute Maximum Rating System (IEC 134) Voltages are referenced to GND (ground = 0V)

FUNCTION TABLE

OPERATING		INP	OUTPUTS			
MODES	MR	СР	D _{sa}	D _{sb}	Q ₀	Q ₁ – Q ₇
Reset (clear)	L	Х	х	х	L	L – L
Shift	нттт	$\leftarrow \leftarrow \leftarrow$	l h h	 h h		$q_0 - q_6$ $q_0 - q_6$ $q_0 - q_6$ $q_0 - q_6$

H = HIGH voltage level h = HIGH voltage level

 HIGH voltage level one set-up time prior to the LOW-to-HIGH CP transition

= LOW voltage level

= LOW voltage level one set-up time prior to the LOW-to-HIGH CP transition

q = Lower case letter indicates the state of referenced input one set-up time prior to the LOW-to-HIGH CP transition

= LOW-to-HIGH clock transition

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage		-0.5 to +7.0	V
±I _{IK}	DC input diode current	$V_{\rm I} < -0.5 \text{ or } V_{\rm I} > V_{\rm CC} + 0.5 V$	20	mA
±Іок	DC output diode current	$V_{\rm O}$ < -0.5 or $V_{\rm O}$ > $V_{\rm CC}$ + 0.5V	50	mA
±IO	DC output source or sink current – standard outputs – bus driver outputs	$-0.5V < V_O < V_{CC} + 0.5V$	25 35	mA
±I _{GND} , ±I _{CC}	DC V _{CC} or GND current for types with –standard outputs –bus driver outputs		50 70	mA
T _{stg}	Storage temperature range		-65 to +150	°C
P _{TOT}	Power dissipation per package –plastic DIL –plastic mini-pack (SO) –plastic shrink mini-pack (SSOP and TSSOP)	for temperature range: -40 to +125°C above +70°C derate linearly with 12mW/K above +70°C derate linearly with 8 mW/K above +60°C derate linearly with 5.5 mW/K	750 500 400	mW

L

L

↑

NOTES:

1. Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

2. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CC}	DC supply voltage	See Note ¹	1.0	3.3	5.5	V
VI	Input voltage		0	-	V _{CC}	V
Vo	Output voltage		0	-	V _{CC}	V
T _{amb}	Operating ambient temperature range in free air	See DC and AC characteristics per device	-40 -40		+85 +125	°C
t _r , t _f	Input rise and fall times except for Schmitt-trigger inputs	$V_{CC} = 1.0V \text{ to } 2.0V \\ V_{CC} = 2.0V \text{ to } 2.7V \\ V_{CC} = 2.7V \text{ to } 3.6V \\ V_{CC} = 3.6V \text{ to } 5.5V$		- - - -	500 200 100 50	ns/V

NOTES:

1. The LV is guaranteed to function down to V_{CC} = 1.0V (input levels GND or V_{CC}); DC characteristics are guaranteed from V_{CC} = 1.2V to V_{CC} = 5.5V.

DC ELECTRICAL CHARACTERISTICS

Over recommended operating conditions voltages are referenced to GND (ground = 0V)

0)///F			L		LIMITS		105-0	
SYMBOL	PARAMETER	TEST CONDITIONS		°C to +8			o +125°C	
			MIN	TYP ¹	MAX	MIN	MAX	
		$V_{CC} = 1.2V$	0.9			0.9		1
VIH	HIGH level Input	$V_{CC} = 2.0V$	1.4			1.4		
	voltage	V _{CC} = 2.7 to 3.6V	2.0			2.0		1
		V _{CC} = 4.5 to 5.5V	0.7*V _{CC}			0.7*V _{CC}		
		V _{CC} = 1.2V			0.3		0.3	
VIL	LOW level Input	$V_{CC} = 2.0V$			0.6		0.6	
12	voltage	V _{CC} = 2.7 to 3.6V			0.8		0.8	
		V _{CC} = 4.5 to 5.5			0.3*V _{CC}		0.3*V _{CC}	
		$V_{CC} = 1.2V$; $V_I = V_{IH}$ or V_{IL} ; $-I_O = 100\mu A$		1.2				
		$V_{CC} = 2.0V; V_I = V_{IH} \text{ or } V_{IL;} - I_O = 100 \mu A$	1.8	2.0		1.8		
V _{OH}	HIGH level output voltage; all outputs	$V_{CC} = 2.7V; V_I = V_{IH} \text{ or } V_{IL;} - I_O = 100 \mu A$	2.5	2.7		2.5		V
	voltago, an outputo	$V_{CC} = 3.0V; V_I = V_{IH} \text{ or } V_{IL;} - I_O = 100 \mu A$	2.8	3.0		2.8		1
		$V_{CC} = 4.5V; V_I = V_{IH} \text{ or } V_{IL;} - I_O = 100 \mu A$	4.3	4.5		4.3		1
V _{ОН}	HIGH level output voltage;	$V_{CC} = 3.0V; V_I = V_{IH} \text{ or } V_{IL;} - I_O = 6mA$	2.40	2.82		2.20		
VОН	STANDARD outputs	$V_{CC} = 4.5$ V; $V_I = V_{IH}$ or $V_{IL;}$ -I _O = 12mA	3.60	4.20		3.50		Ì
V _{OH}	HIGH level output voltage; BUS driver	$V_{CC} = 3.0V; V_I = V_{IH} \text{ or } V_{IL;} - I_O = 8mA$	2.40	2.82		2.20		V
- OH	outputs	$V_{CC} = 4.5V; V_I = V_{IH} \text{ or } V_{IL}; -I_O = 16mA$	3.60	4.20		3.50		
		$V_{CC} = 1.2V; V_I = V_{IH} \text{ or } V_{IL}; I_O = 100 \mu A$		0		L		4
	LOW level output	$V_{CC} = 2.0V; V_I = V_{IH} \text{ or } V_{IL}; I_O = 100\mu A$		0	0.2		0.2	
V _{OL}	voltage; all outputs	$V_{CC} = 2.7V; V_I = V_{IH} \text{ or } V_{IL}; I_O = 100 \mu A$		0	0.2		0.2	V
		$V_{CC} = 3.0V; V_I = V_{IH} \text{ or } V_{IL;} I_O = 100 \mu A$		0	0.2		0.2	
		$V_{CC} = 4.5V; V_I = V_{IH} \text{ or } V_{IL}; I_O = 100 \mu A$		0	0.2		0.2	
V _{OL}	LOW level output voltage;	$V_{CC} = 3.0V; V_I = V_{IH} \text{ or } V_{IL}; I_O = 6mA$		0.25	0.40		0.50	
0L	STANDARD outputs	$V_{CC} = 4.5 V; V_I = V_{IH} \text{ or } V_{IL}; I_O = 12 \text{mA}$		0.35	0.55		0.65	
V _{OL}	LOW level output voltage; BUS driver	$V_{CC} = 3.0V; V_I = V_{IH} \text{ or } V_{IL;} I_O = 8mA$		0.20	0.40		0.50	
· OL	outputs	$V_{CC} = 4.5V; V_I = V_{IH} \text{ or } V_{IL}; I_O = 16\text{mA}$		0.35	0.55		0.65	
I	Input leakage current	V_{CC} = 5.5V; V_{I} = V_{CC} or GND			1.0		1.0	μ/
I _{OZ}	3-State output OFF-state current	$V_{CC} = 5.5$ V; $V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND			5		10	μ/
	Quiescent supply current; SSI	$V_{CC} = 5.5V; V_1 = V_{CC} \text{ or GND}; I_0 = 0$			20.0		40	
Icc	Quiescent supply current; flip-flops	$V_{CC} = 5.5V; V_I = V_{CC} \text{ or GND}; I_O = 0$			20.0		80	μ/
	Quiescent supply current; MSI	$V_{CC} = 5.5V; V_I = V_{CC} \text{ or GND}; I_O = 0$			20.0		160	.
Icc	Quiescent supply current; LSI	$V_{CC} = 5.5V; V_I = V_{CC} \text{ or GND}; I_O = 0$			500		1000	- μ/
ΔI_{CC}	Additional quiescent supply current per input	$V_{CC} = 2.7V$ to 3.6V; $V_1 = V_{CC} - 0.6V$			500		850	μA

NOTES:

1. All typical values are measured at T_{amb} = 25°C.

AC CHARACTERISTICS

 $GND = 0V; t_r = t_f \leq 2.5ns; C_L = 50pF; R_L = 1K\Omega$

SYMBOL	PARAMETER	WAVEFORM	CONDITION		LIMITS 40 to +85 °	°C		IITS +125 °C	UNIT	
			V _{CC} (V)	MIN	TYP ¹	TYP ¹ MAX		MAX		
			1.2	-	75	-	-	-		
			2.0	-	26	39	-	49		
t _{PHL} /t _{PLH}	Propagation delay CP to Q _n	Figure 1	2.7	-	19	29	-	36	ns	
			3.0 to 3.6	-	14 ²	23	-	29		
			4.5 to 5.5	-	12 ³	19	-	24		
			1.2	-	75	-	-	-		
	Development in a defense		2.0	-	26	39	-	49		
t _{PHL}	Propagation delay MR to Q _n	Figure 2	2.7	-	19	29	-	36	ns	
			3.0 to 3.6	-	14 ²	23	-	29		
			4.5 to 5.5	-	12 ³	19	-	24		
			2.0	34	9	-	41	-		
t	Clock pulse width	Figure 1	2.7	25	6	-	30	-	ns	
t _W	HIGH to LOW	Figure i	3.0 to 3.6	20	5 ²	-	24	-	115	
			4.5 to 5.5	13	4 ³		16			
			2.0	34	10	-	41	-		
*	Master reset pulse	Figure 2	2.7	25	8	-	30	-	20	
tw	width; LOW	Figure 2	3.0 to 3.6	20	6 ²	-	24	-	ns	
			4.5 to 5.5	13	5 ³		16			
			1.2	-	30	-	-	-		
			2.0	19	10	-	24	-		
t _{rem}	Removal time MR to CP	Figure 2	2.7	14	8	-	18	-	ns	
			3.0 to 3.6	11	6 ²	-	14	-		
			4.5 to 5.5	8	5 ³		10			
			1.2	-	15	-	-	- 1		
			2.0	22	5	-	26	- 1		
t _{su}	Set-up time D _{sa} , D _{sb} to CP	Figure 3	2.7	16	4	-	19	- 1	ns	
	D _{Sa} , D _{Sb} to Or		3.0 to 3.6	13	3 ²	-	15	-		
			4.5 to 5.5	8	2 ³		10			
			1.2	-	-10	-	-	- 1		
			2.0	5	-3	-	5	-		
t _h	Hold time D _{sa} , D _{sb} to CP	Figure 3	2.7	5	-2	-	5	- 1	ns	
			3.0 to 3.6	5	-2 ²	-	5	-		
			4.5 to 5.5	5	-1 ³		5			
			2.0	14	40	-	12	-		
¢	Maximum clock	Eigure 1	2.7	19	58	-	16	-	N 41 1-	
f _{max}	pulse frequency	Figure 1	3.0 to 3.6	24	70 ²	-	20	-	MHz	
			4.5 to 5.5	36	100 ³		30			

NOTE:

1. Unless otherwise stated, all typical values are at T_{amb} = 25°C.

2. Typical value measured at V_{CC} = 3.3V.

3. Typical value measured at V_{CC} = 5.0V.

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AC WAVEFORMS

 V_M = 1.5V at $V_{CC} \ge 2.7V \le 3.6V$ V_M = 0.5V * V_{CC} at $V_{CC} < 2.7V$ and $\ge 4.5V$ V_{OL} and V_{OH} are the typical output voltage drop that occur with the output load.

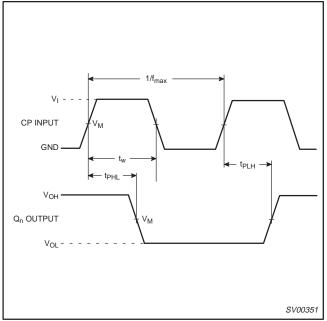


Figure 1. The clock (CP) to output (Q_n) propagation delays, the clock pulse width, the output transition times and the maximum clock pulse frequency

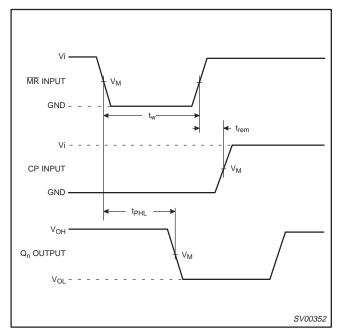


Figure 2. The master reset (MR) pulse width, the master reset to output (Q_n) propagation delay and the master reset to clock (CP) removal time

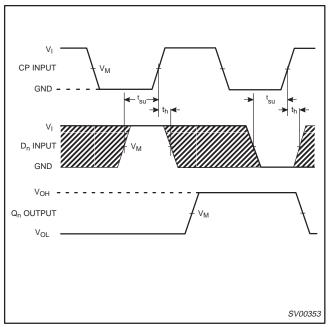


Figure 3. Data set-up and hold times for the D_n inputs

NOTE:

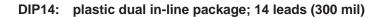
The shaded areas indicate when the input is permitted to change for predictable output performance.

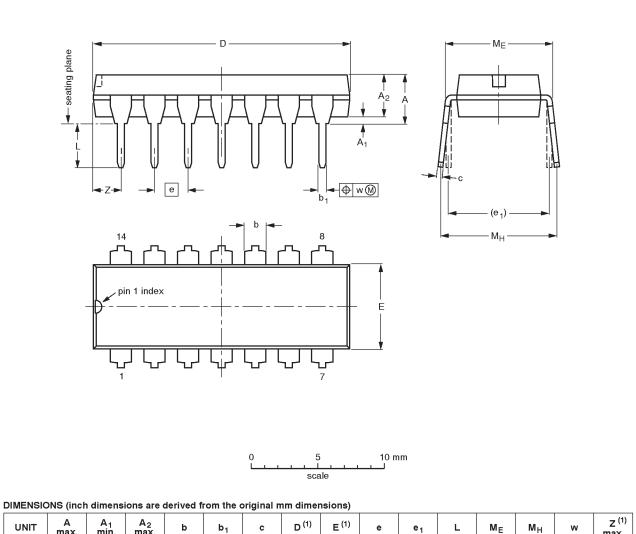
74LV164

TEST CIRCUIT

			PULSE NERATOR	$V_{CC} \xrightarrow{V_{CC}} O_{Open} \xrightarrow{O} O_{Open} $
				Test Circuit for switching times
SWITCH F	POSITION			DEFINITIONS
TEST	S ₁	V _{CC}	VI	R _L = Load resistor; see AC CHARACTERISTICS for value.
t _{PLH} /t _{PHL}	Open	< 2.7V	V _{CC}	C _L = Load capacitance includes jig and probe capacitance: See AC CHARACTERISTICS for value.
t _{PLZ/} t _{PZL}	2 x V _{CC}	2.7–3.6V	2.7V	R_T = Termination resistance should be equal to Z_{OUT} of
t _{PHZ} /t _{PZH}	GND	≥ 4.5V	V _{CC}	pulse generators.
				- SV00755

Figure 4. Load circuitry for switching times





UNIT	max.	min.	max.	b	b ₁	c	D ⁽¹⁾	E ⁽¹⁾	e	e ₁	L	ME	M _H	w	max.
mm	4.2	0.51	3.2	1.73 1.13	0.53 0.38	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.2
inches	0.17	0.020	0.13	0.068 0.044	0.021 0.015	0.014 0.009	0.77 0.73	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.087

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN			
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE		
SOT27-1	050G04	MO-001AA			-92-11-17 95-03-11		

9

Product specification 74LV164

SOT27-1

SO14: plastic small outline package; 14 leads; body width 3.9 mm SOT108-1 А Г Х = v 🕅 A Q 10 (A₃) pin 1 index -p Ι Ш П е detail X bp 2.5 5 mm scale DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	Α3	b _p	c	D ⁽¹⁾	E ⁽¹⁾	е	H _E	L	Lp	Q	v	w	У	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.0098 0.0039		0.01		0.0098 0.0075	0.35 0.34	0.16 0.15	0.050	0.24 0.23	0.041	0.039 0.016	0.028 0.024	0.01	0.01	0.004	0.028 0.012	0°

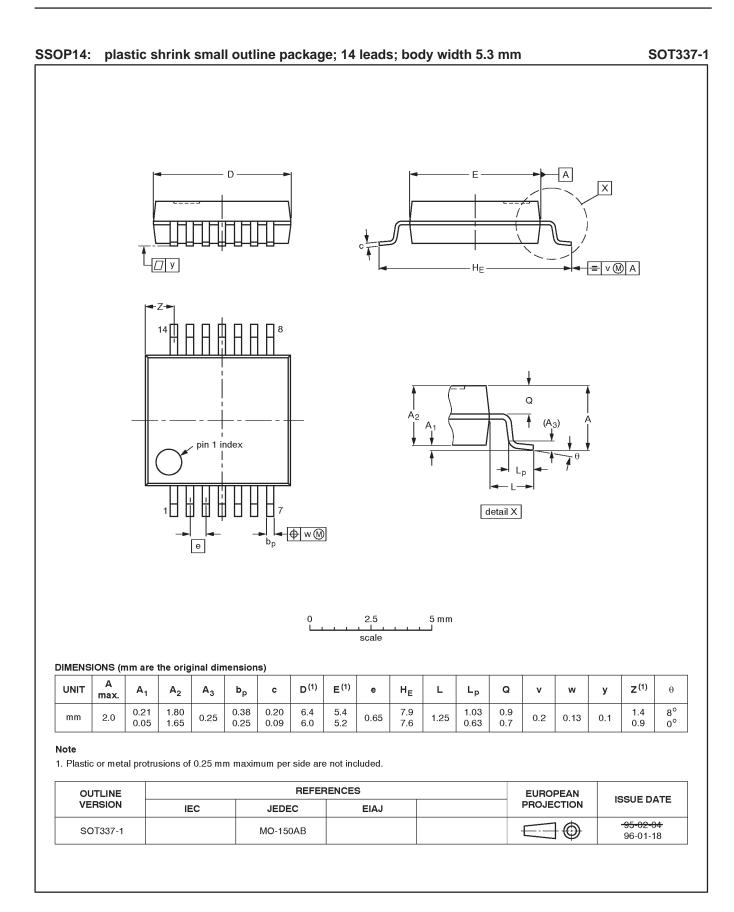
Note

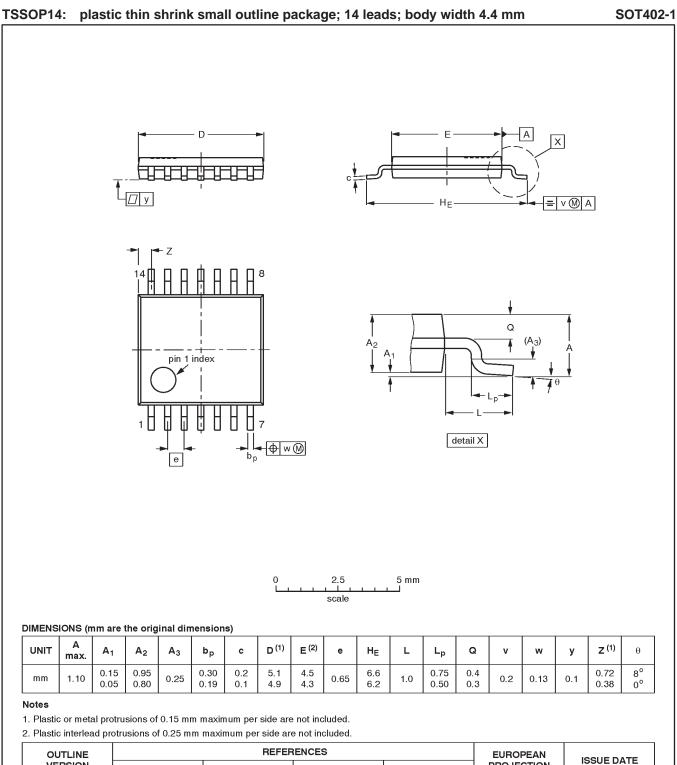
1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN	ISSUE DATE
	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT108-1	076E06S	MS-012AB				91-08-13 95-01-23

Product specification

8-bit serial-in/parallel-out shift register





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DEFINITIONS					
Data Sheet Identification	Product Status	Definition			
Objective Specification	Formative or in Design	This data sheet contains the design target or goal specifications for product development. Specifications may change in any manner without notice.			
Preliminary Specification	Preproduction Product	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.			
Product Specification	Full Production	This data sheet contains Final Specifications. Philips Semiconductors reserves the right to make changes at any time without notice, in order to improve design and supply the best possible product.			

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